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23. (Added) The device as recited in claim 16, wherein said high-K dielectric comprises a metal oxide having a dielectric constant greater than about 20.

24. (Added) A semiconductor device, comprising:

a low-trap-density nitrogen-containing oxide arranged upon an upper surface of a semiconductor substrate, wherein said low-trap-density nitrogen-containing oxide has a thickness of less than about 10 angstroms;

a high-K dielectric having a dielectric constant greater than about 5 arranged upon the nitrogen-containing oxide, wherein said high-K dielectric has a thickness of less than or equal to about 10 angstroms; and

$\beta_1$   
a gate conductor arranged above the high K dielectric.

25. (Added) The device as recited in claim 24, wherein said high-K dielectric comprises silicon nitride.

26. (Added) The device as recited in claim 24, wherein said high-K dielectric comprises a material having a dielectric constant greater than about 20.

27. (Added) The device as recited in claim 24, wherein said high-K dielectric comprises a metal oxide having a dielectric constant greater than about 20.

28. (Added) The device as recited in claim 24, further comprising a dielectric having a dielectric constant greater than about 20 arranged upon the high-K dielectric.